

Divya Somvanshi

List of Publications by Year in descending order

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citing authors

#	ARTICLE	IF	CITATIONS
1	Ultraviolet Detection Properties of p-Si/n-TiO ₂ Heterojunction Photodiodes Grown by Electron-Beam Evaporation and Sol-Gel Methods: A Comparative Study. IEEE Nanotechnology Magazine, 2016, 15, 193-200.	2.0	64
2	Sol-Gel-Based Highly Sensitive Pd/n-ZnO Thin Film/n-Si Schottky Ultraviolet Photodiodes. IEEE Transactions on Electron Devices, 2015, 62, 1879-1884.	3.0	55
3	Nature of carrier injection in metal/2D-semiconductor interface and its implications for the limits of contact resistance. Physical Review B, 2017, 96, .	3.2	55
4	Mean Barrier Height and Richardson Constant for Pd/ZnO Thin Film-Based Schottky Diodes Grown on n-Si Substrates by Thermal Evaporation Method. IEEE Electron Device Letters, 2013, 34, 1238-1240.	3.9	52
5	Analysis of Temperature-Dependent Electrical Characteristics of n-ZnO Nanowires (NWs)/p-Si Heterojunction Diodes. IEEE Nanotechnology Magazine, 2014, 13, 62-69.	2.0	44
6	Improved Current Density and Contact Resistance in Bilayer MoSe ₂ Field Effect Transistors by AlO _x Capping. ACS Applied Materials & Interfaces, 2020, 12, 36355-36361.	8.0	31
7	Effective Richardson Constant of Sol-Gel Derived TiO ₂ Films in n-TiO ₂ /p-Si Heterojunctions. IEEE Electron Device Letters, 2017, 38, 633-636.	3.9	30
8	Pd/ZnO Nanoparticles Based Schottky Ultraviolet Photodiodes Grown on Sn-Coated n-Si Substrates by Thermal Evaporation Method. IEEE Journal of Selected Topics in Quantum Electronics, 2014, 20, 120-125.	2.9	24
9	Analysis of Characteristics of Pd/ZnO Thin Film/n-Si Schottky Diodes with Series Resistance. Journal of Nanoelectronics and Optoelectronics, 2014, 9, 21-26.	0.5	23
10	Electrical and Ultraviolet-A Detection Properties of E-Beam Evaporated n-TiO ₂ Capped p-Si Nanowires Heterojunction Photodiodes. IEEE Nanotechnology Magazine, 2016, , 1-1.	2.0	20
11	Transition metal dichalcogenides based two-dimensional heterostructures for optoelectronic applications. , 2020, , 125-149.		15
12	Ultraviolet Detection Characteristics of Pd/n-ZnO Thin Film Schottky Photodiodes Grown on n-Si Substrates. Journal of Nanoelectronics and Optoelectronics, 2013, 8, 349-354.	0.5	15
13	A systematic study on the electronic structure of 3d, 4d, and 5d transition metal-doped WSe ₂ monolayer. Superlattices and Microstructures, 2020, 148, 106746.	3.1	12
14	Effect of ZnO Seed Layer on the Electrical Characteristics of Pd/ZnO Thin-Film-Based Schottky Contacts Grown on n-Si Substrates. IEEE Nanotechnology Magazine, 2014, 13, 1138-1144.	2.0	11
15	Functionalized polyvinyl chloride/layered double hydroxide nanocomposites and its thermal and mechanical properties. Journal of Applied Polymer Science, 2020, 137, 48894.	2.6	8
16	Effects of Sn and Zn Seed Layers on the Electrical Characteristics of Pd/ZnO Thin-Film Schottky Diodes Grown on n-Si Substrates. IEEE Electron Device Letters, 2014, 35, 945-947.	3.9	7
17	Recent Progress on Extended Wavelength and Split-Off Band Heterostructure Infrared Detectors. Micromachines, 2020, 11, 547.	2.9	6
18	Analysis of Extended Threshold Wavelength Photoresponse in Nonsymmetrical p-GaAs/AlGaAs Heterostructure Photodetectors. IEEE Journal of Selected Topics in Quantum Electronics, 2018, 24, 1-7.	2.9	5

#	ARTICLE	IF	CITATIONS
19	Boosting Principal Component Analysis by Genetic Algorithm. Defence Science Journal, 2010, 60, 392-398.	0.8	5
20	Accuracy of activation energy from Arrhenius plots and temperature-dependent internal photoemission spectroscopy. Infrared Physics and Technology, 2019, 102, 103026.	2.9	4
21	Strain-dependent doping behavior of WSe ₂ monolayer: A first-principle calculation. Europhysics Letters, 2022, 137, 26004.	2.0	4
22	Catalyst free growth of ZnO nanorods by thermal evaporation method. , 2013, , .		3
23	Analysis of Barrier Parameters on the Extended Threshold Wavelength of Infrared Detectors. IEEE Photonics Technology Letters, 2018, 30, 1617-1620.	2.5	3
24	Reduced Dark Current With a Specific Detectivity Advantage in Extended Threshold Wavelength Infrared Detector. , 2019, 3, 1-4.		3
25	First-principal insight of the gold-metal interaction to bilayer MoSe ₂ of AB and AA stacking order. Solid State Communications, 2022, 342, 114613.	1.9	3
26	Fabrication and Characterization of ZnO Nanowires by Thermal Oxidation Method. Advanced Materials Research, 0, 585, 124-128.	0.3	2
27	Electrical and optical characterization of Pd/ZnO nanorods (NRs) Schottky diodes grown on n-Si substrates. , 2014, , .		2
28	Structural and optical characteristics of n-TiO ₂ thin films by sol-gel method. , 2015, , .		2
29	Synthesis and optical properties of zinc oxide nanoparticles grown on Sn-coated silicon substrate by thermal evaporation method. , 2013, , .		1
30	Electrical Characterization of n-ZnO Nanowires/p-Si Based Heterojunction Diodes. Environmental Science and Engineering, 2014, , 589-592.	0.2	1
31	Electrical and Ultraviolet Detection Properties of n-ZnO Thin Film/p-Si Heterojunction Diodes Using a ZnO Buffer Layer. Journal of Nanoelectronics and Optoelectronics, 2015, 10, 219-225.	0.5	1
32	Electrical characteristics of Pd/ZnO nanowires (NWs)-based Schottky diodes grown on Zn seed layercoated n-Si substrates. , 2014, , .		0
33	Optical and Electrical Characterization of n-MoS ₂ /p-Si Heterojunction Diode. , 2020, , .		0
34	Theoretical Insights into Gold Metal Contacts to Monolayer and Bilayer MoSe ₂ . , 2021, , .		0